

Amendment of the Claims

Please amend claims 1 and 7 as indicated below. Please cancel claims 6 and 11.

1. (Currently Amended) A tip attached to a chip component for making a readable change into a storage medium, the tip comprising: a conductive layer;

a tip sub-layer made of amorphous silicon disposed on the conductive layer; and

an outer layer disposed on the tip sub-layer formed of a silicide material;

wherein the chip component is constructed with at least one type of metal material;

wherein the silicide includes a metal having a silicide formation temperature below a melting temperature of the metal material of the chip component wherein the melting temperature is at or below 500 Degrees C.

2. (Original) The tip according to claim 1, wherein the chip component is an IC electrical component.

3. (Original) The memory storage device according to claim 1, further comprising a nitride layer disposed on the outer layer.

4. (Original) The tip according to claim 1, wherein the metal of the silicide is Platinum or Palladium.

5. (Original) The tip according to claim 1, wherein the metal of the silicide is iron, chrome, nickel, niobium, or molybdenum.

6. (Cancelled)

7. (Currently Amended) A memory storage device comprising:

a chip component including a metal material;

a tip connected to the chip;

a storage medium in contact with the tip; wherein the tip comprises: a conductive layer;

a tip sub-layer made of amorphous silicon disposed on the conductive layer; and an outer layer disposed on the tip sub-layer formed of a silicide;

wherein the silicide includes a metal having a silicide formation temperature below a melting temperature of the metal material of the chip component wherein the formation temperature is at or below 500 Degrees C.

8. (Original) The memory storage device according to claim 7, wherein the chip component is an IC electrical component.

9. (Original) The memory storage device according to claim 7, further comprising a nitride layer disposed on the outer layer.

10. (Original) The memory storage device according to claim 7, wherein the metal of the outer layer is platinum or palladium.

11. (Cancelled)

12. (Original) The memory storage device according to claim 7, wherein the metal of the outer layer is iron, chrome, nickel, niobium, or molybdenum.

13-22. (Cancelled)